

TOSHIBA Diode Silicon Epitaxial Planar Type

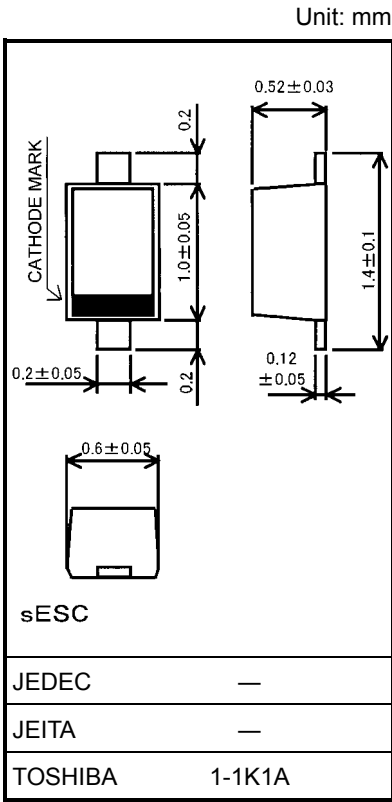
JDV2S09S

VCO for UHF band

- High capacitance ratio: $C_{1V}/C_{4V} = 2.1$ (typ.)
- Low series resistance: $r_s = 0.33\ \Omega$ (typ.)
- This device is suitable for use in a small-size tuner.

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Reverse voltage	V_R	10	V
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-55~150	°C



Electrical Characteristics (Ta = 25°C)

Weight: 0.0011 g (typ.)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse voltage	V_R	$I_R = 1\ \mu A$	10	—	—	V
Reverse current	I_R	$V_R = 10\ V$	—	—	3	nA
Capacitance	C_{1V}	$V_R = 1\ V, f = 1\ MHz$	9.7	—	11.1	pF
	C_{4V}	$V_R = 4\ V, f = 1\ MHz$	4.45	—	5.45	
Capacitance ratio	C_{1V}/C_{4V}	—	1.8	2.1	—	—
Series resistance	r_s	$V_R = 1\ V, f = 470\ MHz$	—	0.33	0.45	Ω

Note: Signal level when capacitance is measured. $V_{sig} = 500\ mV_{rms}$

Marking

